



PATENT APPLICATION  
Docket No. 9898-206  
Client No. SS-15638-US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:	Shin Kim, et al	Conf. No.	6784
Serial No.	10/068,628	Examiner:	Dinh, Tuan T.
Filed:	February 6, 2002	Art Unit:	2827
For:	SEMICONDUCTOR DEVICE BONDING PAD RESISTANT TO STRESS AND METHOD OF FABRICATING THE SAME		

Mail Stop Issue Fee  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**APPLICANT'S COMMENTS ON EXAMINER'S STATEMENT OF REASONS FOR  
ALLOWANCE**

Applicant submits that the prior art alone or in combination does not teach a bonding pad structure of a semiconductor device, said bonding pad structure comprising: a substructure formed on a semiconductor substrate; a first dielectric layer formed on the substructure; a polysilicon film plate formed on the first dielectric layer; a second dielectric layer formed overlying the polysilicon film plate, the second dielectric layer having a first opening that expose a region of the polysilicon film plate, a first metal layer formed on the polysilicon film plate through the first opening; an inter-metal dielectric (IMD) layer formed overlying the first metal layer, the inter-metal dielectric layer having a second opening that exposes a region of the first metal layer; a second metal layer formed on the first metal layer in the second opening; and a passivation layer formed overlying the second metal layer, the passivation layer having a third opening that exposes a region of the second metal layer as a bonding pad, the bonding pad positioned above and overlapping the polysilicon film plate, as recited in allowed claim 1. Applicant submits that the prior art alone or in combination does not teach a bonding pad structure of a semiconductor device, said bonding pad structure comprising: a substructure formed on a semiconductor substrate; a first dielectric layer formed on the substructure; a polysilicon film plate formed on the first dielectric layer; a second dielectric layer formed overlying the polysilicon film plate, the second dielectric layer having a first opening that expose a region of the polysilicon film plate, a first metal layer

formed directly on the polysilicon film plate through the first opening; an inter-metal dielectric (IMD) layer formed overlying the first metal layer, the inter-metal dielectric layer having a second opening that exposes a region of the first metal layer; a second metal layer formed directly on the first metal layer in the second opening; and a passivation layer formed overlying the second metal layer, the passivation layer having a third opening that exposes a region of the second metal layer as a bonding pad, the bonding pad overlying the polysilicon film plate, as recited in allowed claim 23.

The remaining claims further distinguish over the prior art.

**Customer No. 20575**

Respectfully submitted,

MARGER JOHNSON & McCOLLOM, P.C.



Hosoon Lee  
Limited Recognition Under 37 CFR § 10.9(b)

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Li Mei Vermilya



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**TRANSMITTAL LETTER**

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Enclosed for filing in the above-referenced application are the following:

- ☒ Publication and Issue Fee
- ☒ TWO Replacement sheet(s) of Formal drawings (comprises 6 figures)
- ☒ Letter to Official Draftsman
- ☒ Applicant's Comments on Examiner's Statement of Reasons For Allowance
- ☒ In connection with issuance of a patent:
  - ☐ Supplemental Declaration      ☒ PTO Form 85B
- ☒ Limited Recognition Under 37 CFR § 10.9(b)
- ☒ PTO Form 2038 authorizing credit card payment for the above-listed fees
- ☒ Any deficiency or overpayment should be charged or credited to deposit account number 13-1703. A duplicate copy of this sheet is enclosed.

**Customer No. 20575**

Respectfully submitted,  
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